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| U.S. Department of Commerce, Patent and Trademark | | Atty. Docket No. | Application No. |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT | | SNDK.256US0 | 10/052,924 |
| | | Applicant(s) | |
| QTP (Use several sheets if necessary) | | Mokhlesi et al. | |
| | | Filing Date | Group |
| | | January 18, 2002 | 2818 |

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| Examiner | Huan Hoang | Date Considered |

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